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For earth 1449 (Modified)							Atty. Docket No. 27/217			Application No. 10/632,955			
INFORMATION DISCLOSURE CITATION IN AN APPLICATION (USE SEVERAL SHEETS IF NECESSARY)							Applicant: Nathan et al						
							Filing Date: 04 Aug 2003			Group Art Unit: 2913			
U.S. PATENT DOCUMENTS													
	EXAMINI INITIAL		DOCUMENT NUMBER		DATE		NAME .			CLASS	SUB- CLASS	FILING DATE	
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AF	Mais	A Three Dimensional Optical Photonic Crystal, Lin et al, Journal Of Lightwave Technology Vol.17, no.11 Nov '99											
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EXAN if not	EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformation and not considered. Include copy of this form with next communication to applicant.												

Sheet 2 of 2 Form PTO-1449 (Modified) Atty. Docket No. Application No. SEP 1 5 2003 27/217 10/632.955 INFORMATION DISCLOSURE CIT IN AN APPLICA FORMS Applicant: Nathan et al (USE SEVERAL SHEETS IF NECESSARY) Group Art Unit: 2813 Filing Date: 04 Aug 2003 **U.S. PATENT DOCUMENTS EXAMINER** DOCUMENT-DATE NAMÉ **CLASS** SUB-**FILING** INITIAL NUMBER **CLASS** DATE BA BB FOREIGN PATENT DOCUMENTS DOCUMENT DATE COUNTRY CLASS SUB-CLASS **TRANSLATION** MUMBER YES NO BC OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.) BD Electrooptical Effects in Silicon, Soref et al; Jl of Quantum Electronics, vol. QE-23, no. 1 Jan 87 pp.123-129 BE Fabrication of a narrow gold wire using scanning tunneling microscopy; Okamoto et al; , Jpn J Appl Phys, Vol 36 (1997) Pt 1, No. 6B pp.3832-3833 BF Fabrication and direct transmission measurement of high-aspect-ratio two-dimensional silicon-based photonic crystal chips, Xu et al, J Opt Soc Am B/Vol 18 No. 8 August 2001pp.1084-1091 BG Defect Modes in Two-Dimensional Triangular Photonic Crystals. X. P. Feng et al , Jpn. J. Appl. Phys., 36 pp. L120-L123, 1997 BH Narrow Band Microcavity Waveguides In Photonic Crystals, Boag et al, J. Opt. Soc. Am. A, 18(11) pp. 2799-2805, 2001 ΒI Bipolar Semiconductor Devices; Roulston; Section 3.5.2, Mc-Graw Hill 1990, ISBN 0-07-054120-5, BJ Photonic Crystals: putting a new twist on light, Joannopoulus et al., Nature, vol. 386, Mar. 13, 1997, pp. 143-BK Design And Sensitivity Analysis Of Narrow Band Photonic Waveguides, Boag et al, URSI Radio Science Meeting, Boston, MA, July 2001, pp 33-35 BL Chapter 55 of the "Complete guide to semiconductor devices" by Kwok K. Ng, Mc-Graw Hill, 1995, ISBN 0-07-035860-5, pp 441-445 Chapter 15 of the "Complete guide to semiconductor devices" by Kwok K. Ng, Mc-Graw Hill, 1995, ISBN 0-07-035860-5, pp. 132-143 **EXAMINER DATE CONSIDERED** EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation

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